Preferred Device

Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors

PNPN devices designed for high volume, low cost consumer applications such as temperature, light and speed control; process and remote control; and warning systems where reliability of operation is critical.

Features

- Small Size
- Passivated Die Surface for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Recommend Electrical Replacement for C106
- Surface Mount Package Case 369C
- To Obtain "DPAK" in Straight Lead Version (Shipped in Sleeves): Add '1' Suffix to Device Number, i.e., MCR706A1
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Human Body Model, 3B > 8000 V • ESD Ratings: Machine Model, C > 400 V
- Pb-Free Packages are Available

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

$\begin{tabular}{ c c c c c c } \hline Rating & Symbol & Max & Unit \\ \hline Peak Repetitive Off-State Voltage (Note 1) \\ (T_{C} = -40 to +110 °C, Sine Wave, 50 to 60 Hz, \\ R_{GK} = 1 k\Omega) & MCR703A \\ MCR706A & MCR708A & 100 \\ \hline MCR708A & MCR708A & 600 & \\ \hline Peak Non-Repetitive Off-State Voltage \\ (Sine Wave, 50 to 60 Hz, R_{GK} = 1 k\Omega, \\ T_{C} = -40 to +110 °C) & MCR703A \\ MCR706A & 450 \\ \hline MCR706A & 450 \\ \hline MCR706A & \\ MCR708A & \\ \hline MOR708A & \\ \hline MCR708A & \\ \hline MOR708A & \\ \hline MOR708A$, , , , , , , , , , , , , , , , , , ,						
$ \begin{array}{c c} (T_{C} = -40 \ \text{to} +110^{\circ}\text{C}, \ \text{Sine Wave, 50 to 60} \ \text{Hz}, \\ R_{GK} = 1 \ \text{k}\Omega) & \text{MCR703A} \\ R_{GK} = 1 \ \text{k}\Omega) & \text{MCR708A} & 100 \\ \text{MCR708A} & 000 \\ \end{array} \\ \begin{array}{c c} Peak \ \text{Non-Repetitive Off-State Voltage} \\ (Sine Wave, 50 \ \text{to} 60 \ \text{Hz}, \ R_{GK} = 1 \ \text{k}\Omega, \\ T_{C} = -40 \ \text{to} +110^{\circ}\text{C}) & \text{MCR703A} \\ \text{MCR708A} & 150 \\ \text{MCR708A} & 650 \\ \end{array} \\ \begin{array}{c c} Peak \ \text{Non-Repetitive Off-State Voltage} \\ (Sine Wave, 50 \ \text{to} 60 \ \text{Hz}, \ R_{GK} = 1 \ \text{k}\Omega, \\ T_{C} = -40 \ \text{to} +110^{\circ}\text{C}) & \text{MCR703A} \\ \text{MCR708A} & 650 \\ \end{array} \\ \begin{array}{c c} On-State \ \text{RMS Current} \\ (180^{\circ} \ \text{Conduction Angles}; \ T_{C} = 90^{\circ}\text{C}) \\ \hline \text{Average On-State Current} (180^{\circ} \ \text{Conduction} \\ \text{Angles} & \ T_{C} = -40 \ \text{to} +90^{\circ}\text{C} \\ T_{C} = +100^{\circ}\text{C} \\ \hline \text{T}_{C} = +100^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c c} I_{T}(\text{AV}) \\ (1/2 \ \text{Sine Wave, 60 \ Hz}, \ T_{J} = 110^{\circ}\text{C}) \\ (1/2 \ \text{Sine Wave, 1.5 ms, } \ T_{J} = 110^{\circ}\text{C}) \\ \hline \text{Circuit Fusing (t = 8.3 \ \text{msec})} \\ \hline \text{Forward Peak Gate Power} \\ (Pulse \ Width \le 1.0 \ \mu \text{sec}, \ T_{C} = 90^{\circ}\text{C}) \\ \hline \text{Forward Average Gate Power} \\ (t = 8.3 \ \text{msec}, \ T_{C} = 90^{\circ}\text{C}) \\ \hline \text{Forward Peak Gate Current} \\ \hline \text{I}_{GM} \\ \hline \text{O.2} \ A \end{array}$	Rating	Symbol	Max	Unit			
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ (T_C = -40 \text{ to } +110^\circ\text{C}, \text{ Sine Wave, } 50 \text{ to } 60 \text{ Hz}, \\ R_{GK} = 1 \mathrm{k}\Omega) \\ $	V _{DRM,} V _{RRM}	400	V			
$\begin{array}{ c c c c c } \hline (180^{\circ} \mbox{ Conduction Angles; } T_C = 90^{\circ} \mbox{C}) & \hline T_{(1400)} & \hline T_{(1400)} & \hline T_{(1400)} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = +100^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = +100^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = +100^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 90^{\circ} \mbox{C} & \hline T_C = -40 \ to + 10^{\circ} \mbox{C} & \hline T_C = -40 \ to + 10^{\circ} \mbox{C} & \hline T_C = -40^{\circ} \mbox{C} & \hline T_C = -40$		V _{RSM}	450	V			
$\begin{array}{c c} \mbox{Angles} & T_C = -40 \mbox{ to } +90^\circ C & 1.6$		I _{T(RMS)}	4.0	A			
	Angles) $T_{\rm C} = -40$ to +90°C	I _{T(AV)}		A			
$ \begin{array}{c c c c c c } \hline Forward Peak Gate Power & P_{GM} & 0.5 & W \\ \hline (Pulse Width \leq 1.0 \ \mu sec, \ T_C = 90^\circ C) & P_{G(AV)} & 0.1 & W \\ \hline Forward Average Gate Power & P_{G(AV)} & 0.1 & W \\ \hline (t = 8.3 \ m sec, \ T_C = 90^\circ C) & I_{GM} & 0.2 & A \\ \hline Forward Peak Gate Current & I_{GM} & 0.2 & A \\ \hline \end{array} $	(1/2 Sine Wave, 60 Hz, T _J = 110°C)	I _{TSM}		A			
$\begin{tabular}{ c c c c c } \hline (Pulse Width \le 1.0 \ \mu sec, \ T_C = 90 \ ^\circ C) & & & & & \\ \hline Forward Average Gate Power & & P_{G(AV)} & 0.1 & W \\ \hline (t = 8.3 \ msec, \ T_C = 90 \ ^\circ C) & & & & \\ \hline Forward Peak Gate Current & & I_{GM} & 0.2 & A \\ \hline \end{tabular}$	Circuit Fusing (t = 8.3 msec)	l ² t	2.6	A ² sec			
(t = 8.3 msec, $T_C = 90^{\circ}C$) $G(W)$ Forward Peak Gate Current I_{GM} 0.2		P _{GM}	0.5	W			
Civi		P _{G(AV)}	0.1	W			
		I _{GM}	0.2	A			
Operating Junction Temperature Range T _J -40 to +110 °C	Operating Junction Temperature Range	TJ	-40 to +110	°C			
Storage Temperature Range T _{stg} -40 to +150 °C	Storage Temperature Range	T _{stg}	-40 to +150	°C			



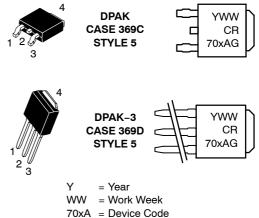
ON Semiconductor®

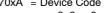
http://onsemi.com

SCRs 4.0 AMPERES RMS 100 - 600 VOLTS









x = 3, 6 or 8 G = Pb-Free Package

PIN ASSIGNMENT				
1	Gate			
2	Anode			
3	Cathode			
4	Anode			

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

2. Case 369C when surface mounted on minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				*	•	•
Peak Repetitive Forward or Reverse Blocking Current (V _{AK} = Rated V _{DRM} or V _{RRM} ; R _{GK} = 1 k Ω)	T _C = 25°C T _C = 110°C	I _{DRM} , I _{RRM}			10 200	μΑ
ON CHARACTERISTICS					•	
Peak Forward "On" Voltage (I _{TM} = 8.2 A Peak, Pulse Width = 1 to 2 ms, 2% Duty Cyc	V _{TM}	-	-	2.2	V	
Gate Trigger Current (Continuous dc) (Note 3) (V_{AK} = 12 Vd	c, $R_L = 24 \Omega$) $T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	I _{GT}		25 -	75 300	μΑ
Gate Trigger Voltage (Continuous dc) (Note 3) $(V_{AK} = 12 \text{ Vdc}, R_L = 24 \Omega)$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	V _{GT}	-		0.8 1.0	V
Gate Non-Trigger Voltage (Note 3) (V _{AK} = 12 Vdc, R_L = 100	Ω, T _C = 110°C)	V _{GD}	0.2	-	-	V
Holding Current (V _{AK} = 12 Vdc, R_{GK} = 1 k Ω) T _C = 25°C (Initiating Current = 20 mA) T _C = -40°C		Ι _Η			5.0 10	mA
Peak Reverse Gate Blocking Voltage (I _{GR} = 10 μ A)		V _{RGM}	10	12.5	18	V
Peak Reverse Gate Blocking Current (V _{GR} = 10 V)		I _{RGM}	-	-	1.2	μA
Total Turn-On Time (Source Voltage = 12 V, $R_S = 6 k\Omega$) ($I_{TM} = 8.2 A$, $I_{GT} = 2 mA$, Rated V_{DRM}) (Rise Time = 20 ns, Pulse Width = 10 µs)		t _{gt}	-	2.0	-	μs
DYNAMIC CHARACTERISTICS				•	•	
Critical Rate of Rise of Off–State Voltage (V_D = Rated V_{DRM} , R_{GK} = 1 k Ω , Exponential Waveform,	T _C = 110°C)	dv/dt	-	10	-	V/µs
Repetitive Critical Rate of Rise of On–State Current (Cf = 60 Hz, I _{PK} = 30 A, PW = 100 μs, diG/dt = 1 A/μs)		di/dt	-	-	100	A/μs
			-			

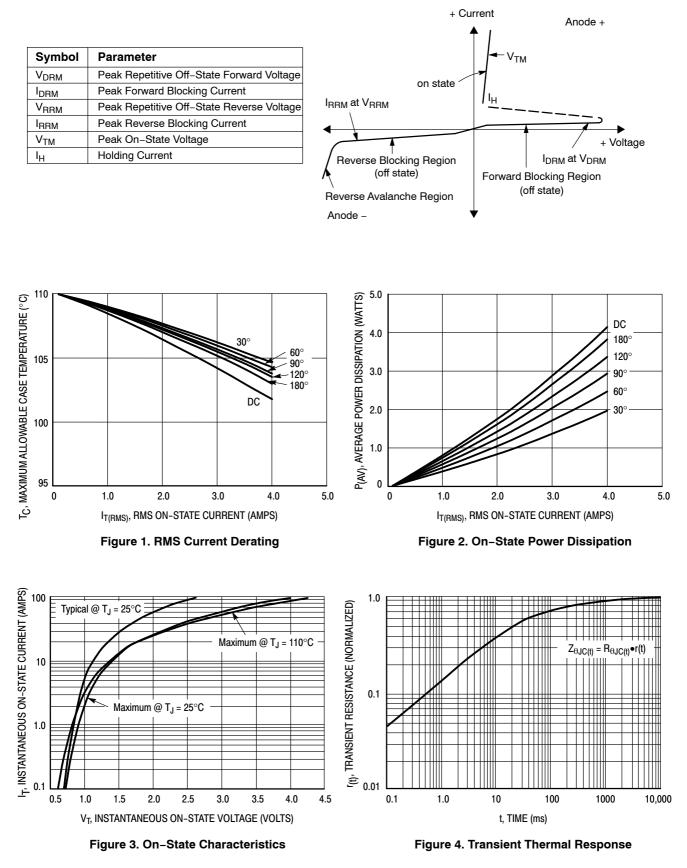
3. R_{GK} current not included in measurement.

ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MCR703AT4	DPAK	369C	2500 Tape & Reel
MCR703AT4G	DPAK	369C (Pb-Free)	2500 Tape & Reel
MCR706AT4	DPAK	369C	2500 Tape & Reel
MCR706AT4G	DPAK	369C (Pb-Free)	2500 Tape & Reel
MCR708A	DPAK	369C	75 Units / Rail
MCR708AG	DPAK	369C (Pb-Free)	75 Units / Rail
MCR708A1	DPAK-3	369D	75 Units / Rail
MCR708A1G	DPAK-3	369D (Pb-Free)	75 Units / Rail
MCR708AT4	DPAK	369C	2500 Tape & Reel
MCR708AT4G	DPAK	369C (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Voltage Current Characteristic of SCR



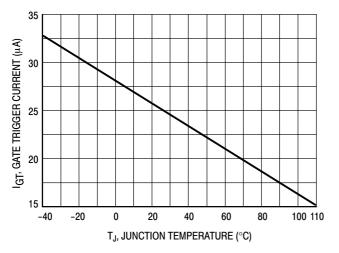


Figure 5. Typical Gate Trigger Current versus Junction Temperature

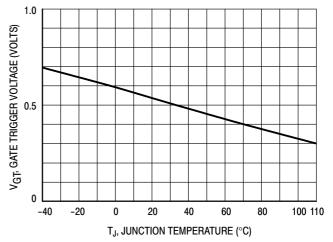


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

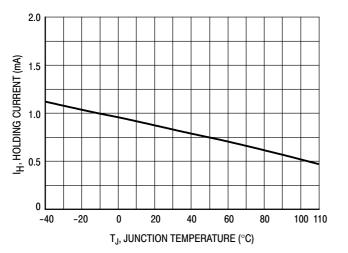


Figure 7. Typical Holding Current versus Junction Temperature

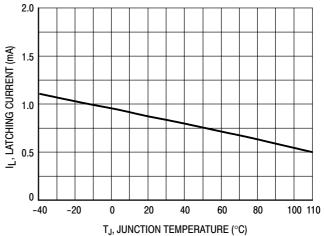
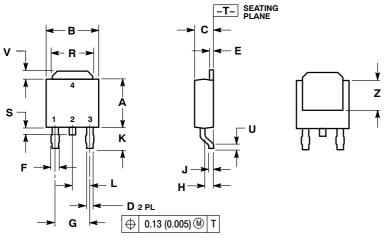


Figure 8. Typical Latching Current versus Junction Temperature

PACKAGE DIMENSIONS

DPAK CASE 369C-01 **ISSUE A**

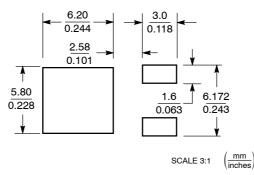


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.22	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.180	BSC	4.58 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
κ	0.102	0.114	2.60	2.89	
L	0.090 BSC		2.29 BSC		
R	0.180	0.215	4.57	5.45	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
V	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

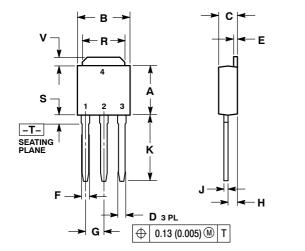
STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE

SOLDERING FOOTPRINT*

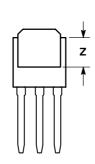


*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS









ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
в	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
κ	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Ζ	0.155		3.93	

STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE

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